

Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

1. (currently amended) A semiconductor device, comprising:
a substrate;
an insulating layer formed on the substrate;
a fin formed on the insulating layer;
silicided source and drain regions formed adjacent the fin, wherein the silicided source and drain regions are silicided down to the insulating layer; and
a metal gate formed over a portion of the fin.

2. (original) The semiconductor device of claim 1 wherein fin includes silicon.

3. (original) The semiconductor device of claim 1, wherein the metal gate includes tantalum or titanium.

4. (original) The semiconductor device of claim 1, further comprising:
at least one dielectric layer formed between the fin and the metal gate.

5. (canceled)

6. (currently amended) The semiconductor device of claim ~~[[5]]~~ 1, wherein the silicided source and drain regions have a thickness ranging from about 400 Å to about 1500 Å.

7. (original) The semiconductor device of claim 1, further comprising:

a pair of spacers formed over portions of the fin and on opposite sides of the metal gate.

8. (original) The semiconductor device of claim 7, wherein the portions of the fin under the pair of spacers separate a channel region of the fin from the silicided source and drain regions.

9-15. (canceled)

16. (currently amended) A semiconductor device, comprising:

a substrate;

an insulating layer formed on the substrate;

a fin formed on the insulating layer;

a dielectric layer formed on the fin;

a metal gate formed over a portion of the fin and the dielectric layer;

a pair of spacers formed on the fin on opposite sides of the metal gate; and

silicided source and drain regions having a thickness ranging from about 400 Å to about 1500 Å formed on the opposite sides of the metal gate.

17. (original) The semiconductor device of claim 16, wherein the metal gate includes tantalum or titanium.

18. (original) The semiconductor device of claim 16, wherein the silicided source and drain regions are composed of silicide down to the insulating layer.

19. (original) The semiconductor device of claim 16, wherein the metal gate and the pair of spacers are located over a channel region of the fin, and

wherein the silicided source and drain regions comprise a silicide material down to the insulating layer.

20. (canceled)